

Quad Bus Buffer With 5 V-Tolerant Inputs

MC74LVX125

The MC74LVX125 is an advanced high speed CMOS quad bus buffer. The inputs tolerate voltages up to 6.5 V, allowing the interface of 5.0 V systems to 3.0 V systems.

The MC74LVX125 requires the 3-state control input (\overline{OE}) to be set High to place the output into the high impedance state.

Features

- High Speed: $t_{PD} = 4.4$ ns (Typ) at $V_{CC} = 3.3$ V
- Low Power Dissipation: $I_{CC} = 4$ μ A (Max) at $T_A = 25^\circ$ C
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise: $V_{OLP} = 0.5$ V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V
- These Devices are Pb-Free and are RoHS Compliant

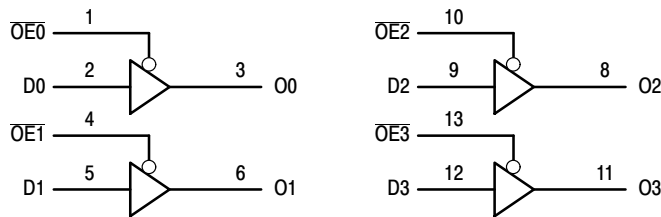


Figure 1. Logic Diagram

PIN NAMES

Pins	Function
\overline{OE}_n	Output Enable Inputs
D_n	Data Inputs
O_n	3-State Outputs

FUNCTION TABLE

INPUTS		OUTPUTS
\overline{OE}_n	D_n	O_n
L	L	L
L	H	H
H	X	Z

H = High Voltage Level; L = Low Voltage Level; Z = High Impedance State; X = High or Low Voltage Level and Transitions Are Acceptable, for I_{CC} reasons, DO NOT FLOAT Inputs

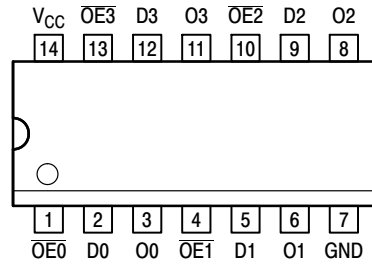


SOIC-14 NB
D SUFFIX
CASE 751A



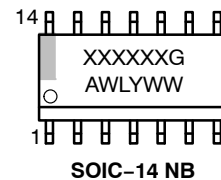
TSSOP-14
DT SUFFIX
CASE 948G

PIN ASSIGNMENT

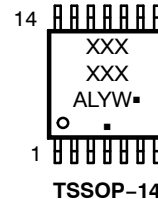


14-Lead (Top View)

MARKING DIAGRAMS



SOIC-14 NB



TSSOP-14

- XXX = Specific Device Code
- A = Assembly Location
- WL, L = Wafer Lot
- Y = Year
- WW, W = Work Week
- G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MC74LVX125

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +6.5	V
V _{in}	DC Input Voltage	-0.5 to +6.5	V
V _{out}	DC Output Voltage	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current	±20	mA
I _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation	SOIC TSSOP 1077 833	mW
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	3.6	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-40	+85	°C
Δt/ΔV	Input Rise and Fall Time	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} V	T _A = 25°C			T _A = -40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	High-Level Input Voltage		2.0	1.5			1.5		V
			3.0	2.0			2.0		
			3.6	2.4			2.4		
V _{IL}	Low-Level Input Voltage		2.0			0.5		0.5	V
			3.0			0.8		0.8	
			3.6			0.8		0.8	
V _{OH}	High-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	I _{OH} = -50μA I _{OH} = -50μA I _{OH} = -4mA	2.0	1.9	2.0		1.9		V
			3.0	2.9	3.0		2.9		
			3.0	2.58			2.48		
V _{OL}	Low-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	I _{OL} = 50μA I _{OL} = 50μA I _{OL} = 4mA	2.0		0.0	0.1		0.1	V
			3.0		0.0	0.1		0.1	
			3.0			0.36		0.44	
I _{in}	Input Leakage Current	V _{in} = 5.5V or GND	3.6			±0.1		±1.0	μA
I _{OZ}	Maximum Three-State Leakage Current	V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	3.6			±0.25		±2.5	μA
I _{CC}	Quiescent Supply Current	V _{in} = V _{CC} or GND	3.6			4.0		40.0	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

MC74LVX125

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0\text{ns}$)

Symbol	Parameter	Test Conditions	$T_A = 25^\circ\text{C}$			$T_A = -40 \text{ to } 85^\circ\text{C}$		Unit
			Min	Typ	Max	Min	Max	
t_{PLH} , t_{PHL}	Propagation Delay Input to Output	$V_{CC} = 2.7\text{V}$ $C_L = 15\text{pF}$		5.8	10.1	1.0	13.5	ns
		$C_L = 50\text{pF}$		8.3	13.6	1.0	17.0	
		$V_{CC} = 3.3 \pm 0.3\text{V}$ $C_L = 15\text{pF}$		4.4	6.2	1.0	8.5	
		$C_L = 50\text{pF}$		6.9	9.7	1.0	12.0	
t_{PZL} , t_{PZH}	Output Enable Time OE to O	$V_{CC} = 2.7\text{V}$ $C_L = 15\text{pF}$		5.3	9.3	1.0	12.5	ns
		$R_L = 1\text{k}\Omega$ $C_L = 50\text{pF}$		7.8	12.8	1.0	16.0	
		$V_{CC} = 3.3 \pm 0.3\text{V}$ $C_L = 15\text{pF}$		4.0	5.6	1.0	7.5	
		$R_L = 1\text{k}\Omega$ $C_L = 50\text{pF}$		6.5	9.1	1.0	11.0	
t_{PLZ} , t_{PHZ}	Output Disable Time OE to O	$V_{CC} = 2.7\text{V}$ $C_L = 50\text{pF}$		10.0	15.7	1.0	19.0	ns
		$R_L = 1\text{k}\Omega$						
		$V_{CC} = 3.3 \pm 0.3\text{V}$ $C_L = 50\text{pF}$		8.3	11.2	1.0	13.0	
		$R_L = 1\text{k}\Omega$						
t_{OSHL} , t_{OSLH}	Output-to-Output Skew (Note 1)	$V_{CC} = 2.7\text{V}$ $C_L = 50\text{pF}$			1.5		1.5	ns
		$V_{CC} = 3.3 \pm 0.3\text{V}$ $C_L = 50\text{pF}$			1.5		1.5	

1. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

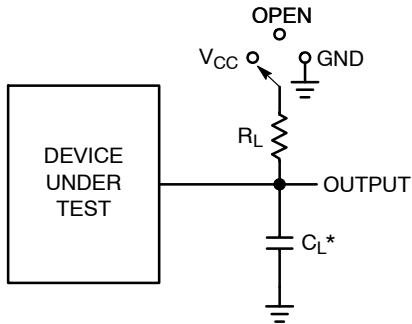
Symbol	Parameter	$T_A = 25^\circ\text{C}$			$T_A = -40 \text{ to } 85^\circ\text{C}$		Unit
		Min	Typ	Max	Min	Max	
C_{in}	Input Capacitance		4	10		10	pF
C_{out}	Maximum Three-State Output Capacitance		6				pF
C_{PD}	Power Dissipation Capacitance (Note 2)		14				pF

2. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}/4$ (per bit). C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0\text{ns}$, $C_L = 50\text{pF}$, $V_{CC} = 3.3\text{V}$, Measured in SOIC Package)

Symbol	Characteristic	$T_A = 25^\circ\text{C}$		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.3	0.5	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	-0.3	-0.5	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

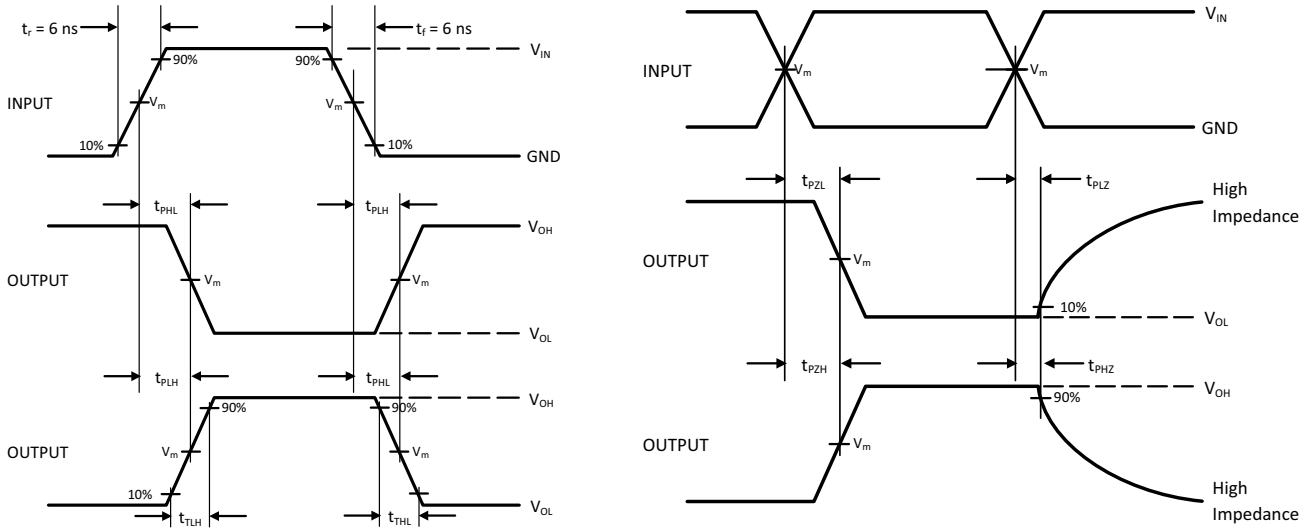
MC74LVX125



*C_L Includes probe and jig capacitance

Test	Switch Position	C _L	R _L
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table	1 kΩ
t _{PLZ} / t _{PZL}	V _{CC}		
t _{PHZ} / t _{PZH}	GND		

Figure 2. Test Circuit



Device	V _{IN} , V	V _m , V
MC74LVX125	V _{CC}	50% x V _{CC}

Figure 3. Switching Waveforms

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MC74LVX125DG	LVX125	SOIC-14 NB	55 Units / Rail
MC74LVX125DR2G	LVX125	SOIC-14 NB	2500 Tape & Reel
MC74LVX125DTG	LVX 125	TSSOP-14	96 Units / Rail
MC74LVX125DTR2G	LVX 125	TSSOP-14	2500 Tape & Reel

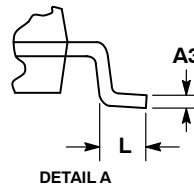
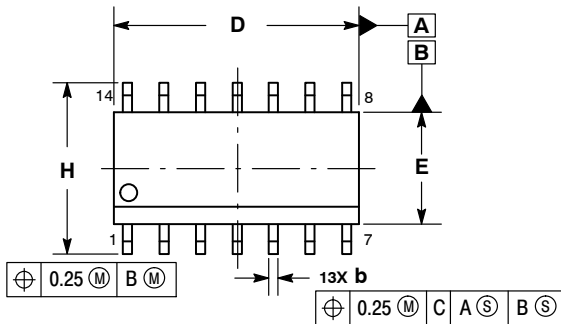
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SCALE 1:1

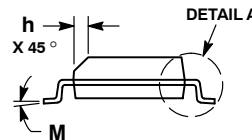
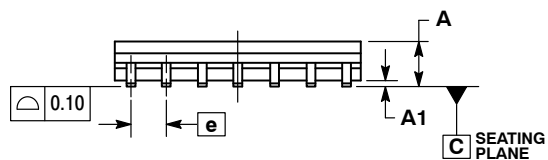
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ISSUE L

DATE 03 FEB 2016

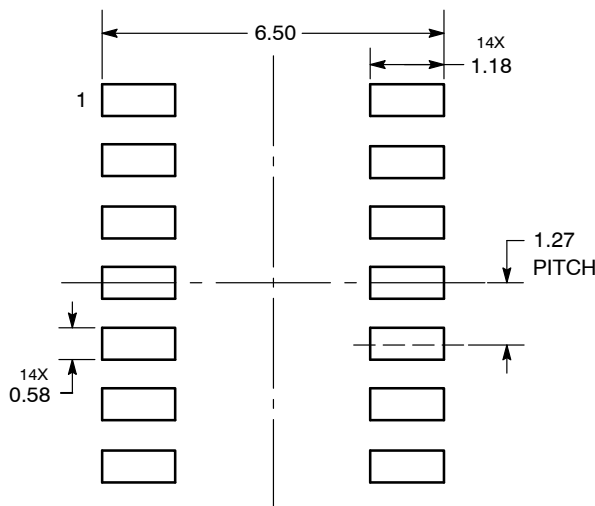


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°



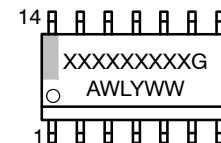
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DATE 03 FEB 2016

STYLE 1:
 PIN 1. COMMON CATHODE
 2. ANODE/CATHODE
 3. ANODE/CATHODE
 4. NO CONNECTION
 5. ANODE/CATHODE
 6. NO CONNECTION
 7. ANODE/CATHODE
 8. ANODE/CATHODE
 9. ANODE/CATHODE
 10. NO CONNECTION
 11. ANODE/CATHODE
 12. ANODE/CATHODE
 13. NO CONNECTION
 14. COMMON ANODE

STYLE 2:
 CANCELLED

STYLE 3:
 PIN 1. NO CONNECTION
 2. ANODE
 3. ANODE
 4. NO CONNECTION
 5. ANODE
 6. NO CONNECTION
 7. ANODE
 8. ANODE
 9. ANODE
 10. NO CONNECTION
 11. ANODE
 12. ANODE
 13. NO CONNECTION
 14. COMMON CATHODE

STYLE 4:
 PIN 1. NO CONNECTION
 2. CATHODE
 3. CATHODE
 4. NO CONNECTION
 5. CATHODE
 6. NO CONNECTION
 7. CATHODE
 8. CATHODE
 9. CATHODE
 10. NO CONNECTION
 11. CATHODE
 12. CATHODE
 13. NO CONNECTION
 14. COMMON ANODE

STYLE 5:
 PIN 1. COMMON CATHODE
 2. ANODE/CATHODE
 3. ANODE/CATHODE
 4. ANODE/CATHODE
 5. ANODE/CATHODE
 6. NO CONNECTION
 7. COMMON ANODE
 8. COMMON CATHODE
 9. ANODE/CATHODE
 10. ANODE/CATHODE
 11. ANODE/CATHODE
 12. ANODE/CATHODE
 13. NO CONNECTION
 14. COMMON ANODE

STYLE 6:
 PIN 1. CATHODE
 2. CATHODE
 3. CATHODE
 4. CATHODE
 5. CATHODE
 6. CATHODE
 7. CATHODE
 8. ANODE
 9. ANODE
 10. ANODE
 11. ANODE
 12. ANODE
 13. ANODE
 14. ANODE

STYLE 7:
 PIN 1. ANODE/CATHODE
 2. COMMON ANODE
 3. COMMON CATHODE
 4. ANODE/CATHODE
 5. ANODE/CATHODE
 6. ANODE/CATHODE
 7. ANODE/CATHODE
 8. ANODE/CATHODE
 9. ANODE/CATHODE
 10. ANODE/CATHODE
 11. COMMON CATHODE
 12. COMMON ANODE
 13. ANODE/CATHODE
 14. ANODE/CATHODE

STYLE 8:
 PIN 1. COMMON CATHODE
 2. ANODE/CATHODE
 3. ANODE/CATHODE
 4. NO CONNECTION
 5. ANODE/CATHODE
 6. ANODE/CATHODE
 7. COMMON ANODE
 8. COMMON ANODE
 9. ANODE/CATHODE
 10. ANODE/CATHODE
 11. NO CONNECTION
 12. ANODE/CATHODE
 13. ANODE/CATHODE
 14. COMMON CATHODE

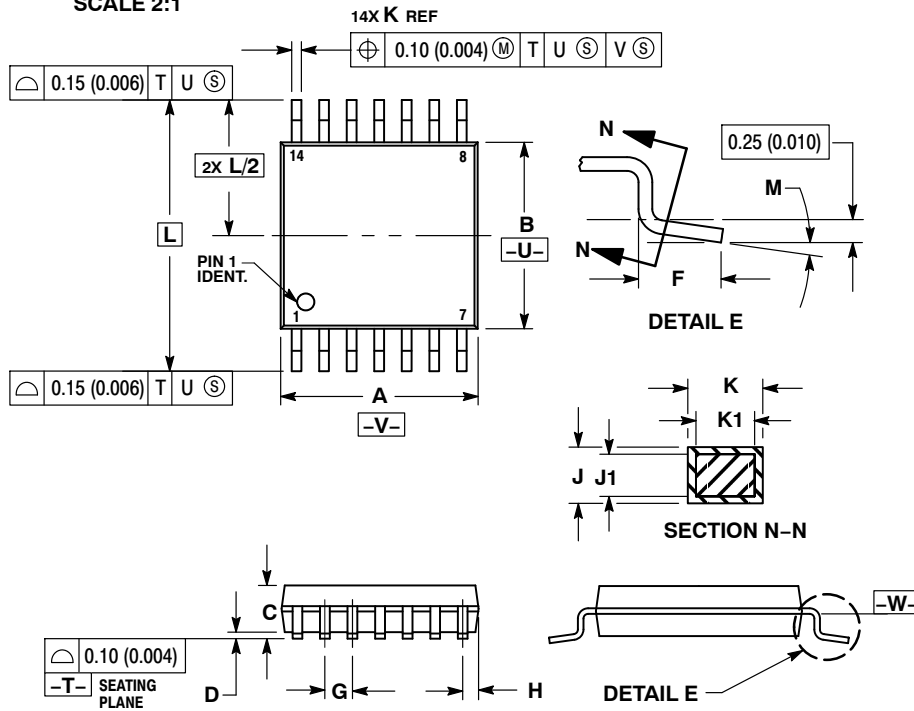
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TSSOP-14 WB
CASE 948G
ISSUE C

DATE 17 FEB 2016



- NOTES:
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 - CONTROLLING DIMENSION: MILLIMETER.
 - DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 - DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 - DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 - TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 - DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

RECOMMENDED
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC
MARKING DIAGRAM*



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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